

**Listing of the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:
  - a substrate;
  - an electrode, the electrode being formed on the substrate;
  - a through-hole being formed through the electrode and the substrate in a stacking direction of the electrode and the substrate, the through-hole having a first diameter in the substrate that is smaller than a second diameter in the electrode;
  - a conductive member being inserted into the through-hole;
  - an insulating material, being disposed between the electrode and the conductive member, the insulating material including a wall portion located higher than at least the electrode; and
  - at least an interlayer dielectric being formed between the substrate and the electrode, the through-hole being formed in the interlayer dielectric, and surfaces of the interlayer dielectric and substrate in the through-hole being formed to have a level difference in a boundary area between the substrate and the interlayer dielectric,
  - the conductive member being formed over the wall portion of the insulating material from the through-hole and being connected with the electrode.
2. (Original) The semiconductor device as defined in claim 1,
  - wherein the insulating material is formed to cover an upper surface of the electrode and a surface in the through-hole, and includes a connection hole for connecting at least the electrode with the conductive member at a position differing from the through-hole, the wall portion being disposed between the connection hole and the through-hole.
- 3-4. (Canceled)

5. (Original) The semiconductor device as defined in claim 1,  
wherein the conductive member functions as a connection terminal which  
secures electrical connection in an axial direction of the through-hole.
6. (Original) The semiconductor device as defined in claim 1,  
wherein a part of the conductive member projects outward from the through-  
hole on a side of the substrate opposite to a side on which the electrode is formed.
7. (Original) A semiconductor device comprising a plurality of the  
semiconductor devices as defined in claim 1 which are stacked, each of the semiconductor  
devices being electrically connected through the conductive members.
8. (Original) A circuit board comprising the semiconductor device as defined in  
claim 1.
9. (Original) An electronic instrument comprising the circuit board as defined in  
claim 8.
- 10-15. (Canceled)